

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device structure, comprising:
 - a substrate defining a substantially horizontal plane;
 - a source region;
 - a drain region;
 - a gate electrode disposed on said substrate and being electrically insulated therefrom, said gate electrode positioned vertically between said source region and said drain region; and
 - a plurality of semiconducting nanotubes, each of said semiconducting nanotubes including a first end electrically coupled with said source region, a second end electrically coupled with said drain region, and a channel region extending vertically through said gate electrode between said source region and said drain region, said channel region being electrically insulated from said gate electrode, and said gate electrode configured to receive a control voltage effective to regulate current flow through said channel region of a respective one of said semiconducting nanotubes between said source region and said drain region.
2. (Previously Presented) The semiconductor device structure of claim 1 wherein said source is composed of a catalyst material effective for growing said semiconducting nanotubes.
3. (Previously Presented) The semiconductor device structure of claim 1 wherein said drain is composed of a catalyst material effective for growing said semiconducting nanotubes.

4. (Original) The semiconductor device structure of claim 1 further comprising:
an insulating layer disposed between said drain and said gate electrode for electrically isolating said drain from said gate electrode.
5. (Original) The semiconductor device structure of claim 1 further comprising:
an insulating layer disposed between said source and said gate electrode for electrically isolating said source from said gate electrode.
6. (Previously Presented) The semiconductor device structure of claim 1 wherein said at least one semiconducting nanotube is composed of arranged carbon atoms.
7. (Cancelled)
8. (Previously Presented) The semiconductor device structure of claim 1 wherein said at least one semiconducting nanotube is oriented substantially perpendicular to said horizontal plane.
9. (Cancelled)
10. (Previously Presented) The semiconductor device structure of claim 1 wherein said gate dielectric is disposed on said semiconducting nanotubes.
- 11-24. (Cancelled)
25. (Currently Amended) A semiconductor device structure, comprising:
a substrate;
an electrically-conductive first plate on said substrate;
an electrically-conductive second plate disposed vertically above said first plate;
an electrically-conductive layer disposed between said first and second plates;

~~at least one nanotube~~ a plurality of nanotubes, each of said nanotubes having an end electrically coupled with said first plate for increasing an effective area of said first plate, ~~said at least one nanotube~~ and each of said nanotubes positioned in said electrically-conductive layer; and

a dielectric layer coating said length of each of said ~~at least one nanotube~~ nanotubes such that said ~~at least one nanotube~~ is nanotubes are electrically isolated from said electrically-conductive layer and said nanotubes are electrically isolated from said second plate.

26. (Original) The semiconductor device structure of claim 25 wherein said at least one nanotube has a conducting molecular structure.

27. (Original) The semiconductor device structure of claim 25 wherein said at least one nanotube has a semiconducting molecular structure.

28. (Original) The semiconductor device structure of claim 25 wherein said dielectric layer encases said at least one nanotube.

29-33. (Cancelled)